September 2009

MCT5201M, MCT5210M, MCT5211M Low Input Current Phototransistor Optocouplers

Features

- High CTR_{CE(SAT)} comparable to Darlingtons
- CTR guaranteed 0°C to 70°C
- High common mode transient rejection 5kV/µs
- Data rates up to 150kbits/s (NRZ)
- Underwriters Laboratory (UL) recognized, file #E90700, volume 2
- IEC60747-5-2 approved (ordering option V)

Applications

- CMOS to CMOS/LSTTL logic isolation
- LSTTL to CMOS/LSTTL logic isolation
- RS-232 line receiver
- Telephone ring detector
- AC line voltage sensing
- Switching power supply

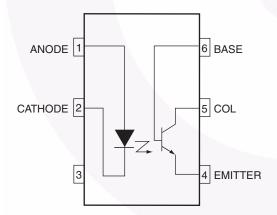
Description

The MCT52XXM series consists of a high-efficiency AlGaAs, infrared emitting diode, coupled with an NPN phototransistor in a six pin dual-in-line package.

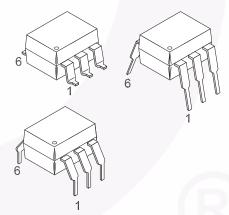
The MCT52XXM is well suited for CMOS to LSTT/TTL interfaces, offering 250% $CTR_{CE(SAT)}$ with 1mA of LED input current. When an LED input current of 1.6mA is supplied data rates to 20K bits/s are possible.

The MCT52XXM can easily interface LSTTL to LSTTL/TTL, and with use of an external base to emitter resistor data rates of 100K bits/s can be achieved.

Schematic



Package Outlines



Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Paramete	Value	Units	
TOTAL DE	VICE			1
T _{STG}	Storage Temperature		-55 to +150	°C
T _{OPR}	Operating Temperature		-40 to +100	°C
T _{SOL}	Lead Solder Temperature		260 for 10 sec	°C
P _D	Total Device Power Dissipation @ 25°C	(LED plus detector)	260	mW
	Derate Linearly From 25°C		3.5	mW/°C
EMITTER				•
I _F	Continuous Forward Current		50	mA
V _R	Reverse Input Voltage		6	V
I _F (pk)	Forward Current - Peak (1 µs pulse, 300	pps)	3.0	А
P_{D}	LED Power Dissipation		75	mW
	Derate Linearly From 25°C		1.0	mW/°C
DETECTOR	2			
I _C	Continuous Collector Current		150	mA
P_{D}	Detector Power Dissipation		150	mW
	Derate Linearly from 25°C		2.0	mW/°C

Electrical Characteristics (T_A = 25°C unless otherwise specified)

Individual Component Characteristics

Symbol	Parameters	Test Conditions	Device	Min.	Тур.*	Max.	Units
EMITTER							'
V _F	Input Forward Voltage	I _F = 5mA	All		1.25	1.5	V
$\frac{\Delta V_F}{\Delta T_A}$	Forward Voltage Temp. Coefficient	I _F = 2mA	All		-1.75		mV/°C
V _R	Reverse Voltage	I _R = 10μA	All	6			V
СЈ	Junction Capacitance	$V_F = 0V, f = 1.0MHz$	All		18		pF
DETECTO	R					•	
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 1.0mA, I _F = 0	All	30	100		V
BV _{CBO}	Collector-Base Breakdown Voltage	$I_C = 10\mu A, I_F = 0$	All	30	120		V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_E = 10\mu A, I_F = 0$	All	5	10		V
I _{CER}	Collector-Emitter Dark Current	$V_{CE} = 10V, I_F = 0,$ $R_{BE} = 1M\Omega$	All		1	100	nA
C _{CE}	Capacitance, Collector to Emitter	V _{CE} = 0, f = 1MHz	All		10		pF
C _{CB}	Capacitance, Collector to Base	V _{CB} = 0, f = 1MHz	All		80		pF
C _{EB}	Capacitance, Emitter to Base	V _{EB} = 0, f = 1MHz	All		15		pF

Isolation Characteristics

Symbol	Characteristic	Test Conditions	Device	Min.	Тур.*	Max.	Units
V _{ISO}	Input-Output Isolation Voltage ⁽¹⁰⁾	f = 60Hz, t = 1 sec.	All	7500			Vac(peak)
R _{ISO}	Isolation Resistance ⁽¹⁰⁾	V _{I-O} = 500 VDC, T _A = 25°C	All	10 ¹¹			Ω
C _{ISO}	Isolation Capacitance ⁽⁹⁾	V _{I-O} = 0, f = 1 MHz	All		0.4	0.6	pF
CM _H	Common Mode Transient	$V_{CM} = 50 V_{P-P1}, R_L = 750\Omega,$ $I_F = 0$	MCT5210M/11M		5000		V/µs
	Rejection – Output HIGH	$V_{CM} = 50 V_{P-P}, R_L = 1K\Omega,$ $I_F = 0$	MCT5201M				
CML	Common Mode Transient	$V_{CM} = 50 V_{P-P1}, R_L = 750\Omega,$ $I_F = 1.6 \text{mA}$	MCT5210M/11M		5000		V/µs
	Rejection – Output LOW	V_{CM} = 50 V_{P-P1} , R_L = 1K Ω , I_F = 5mA	MCT5201M				

^{*}All typical $T_A = 25^{\circ}C$

$\textbf{Electrical Characteristics} \; (\texttt{Continued}) \; (\texttt{T}_{A} = 25 ^{\circ} \texttt{C} \; \text{unless otherwise specified})$

Transfer Characteristics

Symbol	Characteristics	Test Conditions		Device	Min.	Тур.*	Max.	Units
DC CHARA	CTERISTICS							
CTR _{CE(SAT)}	Saturated Current	$I_F = 5mA$, $V_{CE} = 0.4V$		MCT5201M	120			%
	Transfer Ratio ⁽¹⁾ (Collector to Emitter)	I _F = 3.0mA, V _{CE} = 0.4V		MCT5210M	60			
	(Concolor to Limitor)	I _F = 1.6mA, V _{CE} = 0.4V		MCT5211M	100			
		$I_F = 1.0 \text{mA}, V_{CE} = 0.4 \text{V}$			75			
CTR _(CE)	Current Transfer Ratio	I _F = 3.0mA, V _{CE} = 5.0V		MCT5210M				%
	(Collector to Emitter) ⁽¹⁾	I _F = 1.6mA, V _{CE} = 5.0V		MCT5211M	150			
		I _F = 1.0mA, V _{CE} = 5.0V			110			
CTR _(CB)	Current Transfer Ratio	I _F = 5mA, V _{CB} = 4.3V		MCT5201M	0.28			%
	Collector to Base ⁽²⁾	I _F = 3.0mA, V _{CE} = 4.3V		MCT5210M	0.2			
		I _F = 1.6mA, V _{CE} = 4.3V		MCT5211M	0.3			
		I _F = 1.0mA, V _{CE} = 4.3V			0.25			
V _{CE(SAT)}	Saturation Voltage	I _F = 5mA, I _{CE} = 6mA		MCT5201M			0.4	V
		I _F = 3.0mA, I _{CE} = 1.8mA		MCT5210M	1	0.4	1	
		I _F = 1.6mA, I _{CE} = 1.6mA		MCT5211M			0.4	†
AC CHARA	CTERISTICS					-		
T _{PHL}	Propagation Delay HIGH-to-LOW ⁽³⁾	R _L = 330 Ω, R _{BE} = ∞	I _F = 3.0mA,	MCT5210M		10		μs
		$R_L = 3.3 \text{ k}\Omega, R_{BE} = 39 \text{k}\Omega$	$V_{CC} = 5.0V$			7		
		R _L = 750 Ω, R _{BE} = ∞	$I_F = 1.6 \text{mA},$ $V_{CC} = 5.0 \text{V}$ $I_F = 1.0 \text{mA},$ $V_{CC} = 5.0 \text{V}$	MCT5211M		14		
		$R_L = 4.7 \text{ k}\Omega, R_{BE} = 91 \text{k}\Omega$				15		
		$R_L = 1.5 \text{ k}\Omega, R_{BE} = \infty$		1		17		
		$R_L = 10 \text{ k}\Omega, R_{BE} = 160 \text{k}\Omega$				24		
		$V_{CE} = 0.4V, V_{CC} = 5V,$ $R_{L} = \text{fig. } 13, R_{BE} = 330\text{k}\Omega$	I _F = 5mA	MCT5201M		3	30	
T _{PLH}	Propagation Delay LOW-to-HIGH ⁽⁴⁾	R _L = 330 Ω, R _{BE} = ∞	I _F = 3.0mA,	MCT5210M		0.4		μѕ
		$R_L = 3.3 \text{ k}\Omega, R_{BE} = 39 \text{k}\Omega$	$V_{CC} = 5.0V$			8		
		R _L = 750 Ω, R _{BE} = ∞	I _F = 1.6mA,	MCT5211M		2.5		
		$R_L = 4.7 \text{ k}\Omega, R_{BE} = 91 \text{k}\Omega$	$V_{CC} = 5.0V$			11		
		$R_L = 1.5 \text{ k}\Omega, R_{BE} = \infty$	I _F = 1.0mA,			7		
		$R_L = 10 \text{ k}\Omega, R_{BE} = 160 \text{k}\Omega$	$V_{CC} = 5.0V$			16		
		$V_{CE} = 0.4V, V_{CC} = 5V,$ $R_{L} = \text{fig. } 13, R_{BE} = 330\text{k}\Omega$	I _F = 5mA	MCT5201M		12	13	
t _d	Delay Time ⁽⁵⁾	$V_{CE} = 0.4V, R_{BE} = 330k\Omega,$ $R_{L} = 1 k\Omega, V_{CC} = 5V$	I _F = 5mA	MCT5201M		1.1	15	μs
t _r	Rise Time ⁽⁶⁾	$V_{CE} = 0.4V, R_{BE} = 330k\Omega,$ $R_{L} = 1 k\Omega, V_{CC} = 5V$	I _F = 5mA	MCT5201M		2.5	20	μs
t _s	Storage Time ⁽⁷⁾	$V_{CE} = 0.4V, R_{BE} = 330 \text{ k}\Omega,$ $R_{L} = 1 \text{ k}\Omega, V_{CC} = 5V$	I _F = 5mA	MCT5201M		10	13	μs
t _f	Fall Time ⁽⁸⁾	$V_{CE} = 0.4V, R_{BE} = 330 \text{ k}\Omega,$ $R_{L} = 1 \text{ k}\Omega, V_{CC} = 5V$	I _F = 5mA	MCT5201M		16	30	μs

^{*}All typicals at $T_A = 25^{\circ}C$

Notes:

- 1. DC Current Transfer Ratio (CTR_{CE}) is defined as the transistor collector current (I_{CE}) divided by the input LED current (I_F) x 100%, at a specified voltage between the collector and emitter (V_{CE}).
- 2. The collector base Current Transfer Ratio (CTR_{CB}) is defined as the transistor collector base photocurrent(I_{CB}) divided by the input LED current (I_F) time 100%.
- 3. Referring to Figure 14 the T_{PHL} propagation delay is measured from the 50% point of the rising edge of the data input pulse to the 1.3V point on the falling edge of the output pulse.
- 4. Referring to Figure 14 the T_{PLH} propagation delay is measured from the 50% point of the falling edge of data input pulse to the 1.3V point on the rising edge of the output pulse.
- 5. Delay time (t_d) is measured from 50% of rising edge of LED current to 90% of Vo falling edge.
- 6. Rise time (t_r) is measured from 90% to 10% of Vo falling edge.
- 7. Storage time (t_s) is measured from 50% of falling edge of LED current to 10% of Vo rising edge.
- 8. Fall time (t_f) is measured from 10% to 90% of Vo rising edge.
- 9. CISO is the capacitance between the input (pins 1, 2, 3 connected) and the output, (pin 4, 5, 6 connected).
- 10. Device considered a two terminal device: Pins 1, 2, and 3 shorted together, and pins 5, 6 and 7 are shorted together.

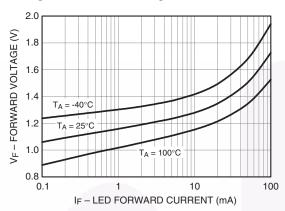
Safety and Insulation Ratings

As per IEC 60747-5-2, this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

Symbol	Parameter	Min.	Тур.	Max.	Unit
	Installation Classifications per DIN VDE 0110/1.89 Table 1				
	For Rated Main Voltage < 150Vrms For Rated Main voltage < 300Vrms		I-IV		
			I-IV		
	Climatic Classification		55/100/21		
	Pollution Degree (DIN VDE 0110/1.89)		2		
CTI	Comparative Tracking Index	175			
V _{PR}	Input to Output Test Voltage, Method b, V _{IORM} x 1.875 = V _{PR} , 100% Production Test with tm = 1 sec, Partial Discharge < 5pC	1594			V _{peak}
	Input to Output Test Voltage, Method a, V _{IORM} x 1.5 = V _{PR} , Type and Sample Test with tm = 60 sec, Partial Discharge < 5pC	1275			V _{peak}
V _{IORM}	Max. Working Insulation Voltage	850			V _{peak}
V_{IOTM}	Highest Allowable Over Voltage	6000			V _{peak}
	External Creepage	7			mm
	External Clearance	7	1		mm
	Insulation Thickness	0.5			mm
RIO	Insulation Resistance at Ts, V _{IO} = 500V	10 ⁹			Ω

Typical Performance Curves

Fig. 1 LED Forward Voltage vs. Forward Current



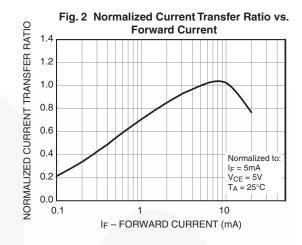


Fig. 3 Normalized CTR vs. Temperature

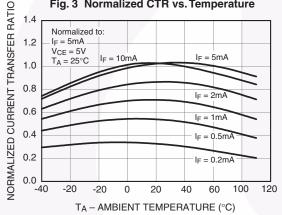


Fig. 4 Normalized Collector vs. Collector-Emitter Voltage

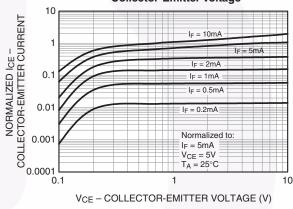


Fig. 5 Normalized Collector Base Photocurrent **Ratio vs. Forward Current**

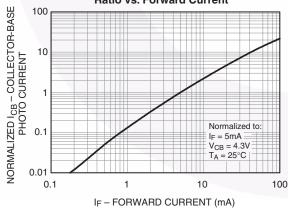
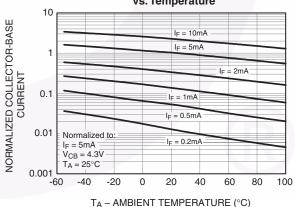


Fig. 6 Normalized Collector-Base Current vs. Temperature



Typical Performance Curves (Continued)

Fig. 7 Collector-Emitter Dark Current vs.
Ambient Temperature

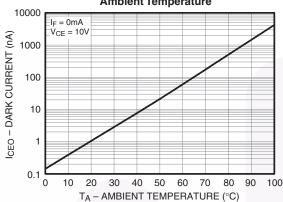


Fig. 9 Switching Time vs. Ambient Temperature

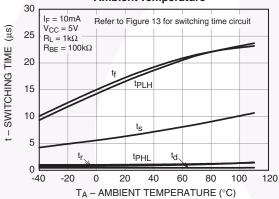


Fig. 11 Switching Time vs. Ambient Temperature

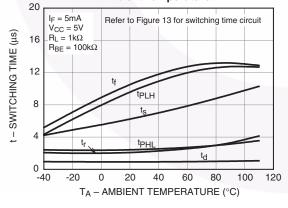


Fig. 8 Switching Time vs. Ambient Temperature

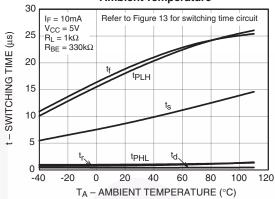


Fig. 10 Switching Time vs. Ambient Temperature

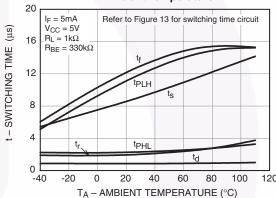
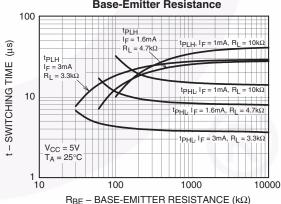


Fig. 12 Switching Time vs. Base-Emitter Resistance



Typical Electro-Optical Characteristics (T_A = 25°C unless otherwise specified)

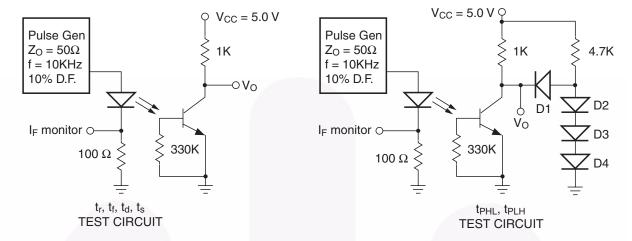


Figure 13.

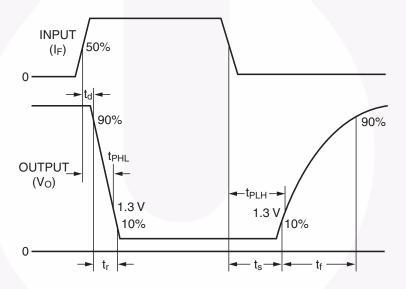
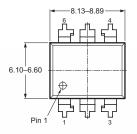
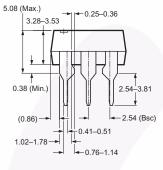


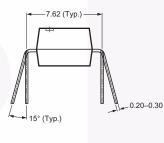
Figure 14. Switching Circuit Waveforms

Package Dimensions

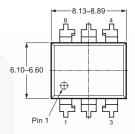
Through Hole

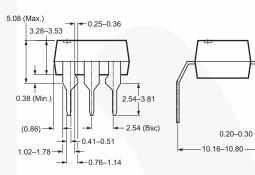




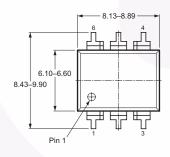


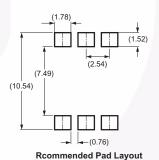
0.4" Lead Spacing

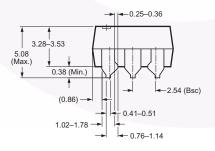


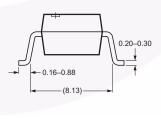


Surface Mount







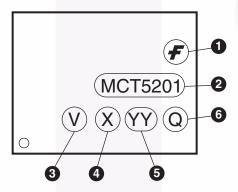


Note: All dimensions in mm.

Ordering Information

Option	Order Entry Identifier (Example)	Description			
No suffix	MCT5201M	Standard Through Hole Device (50 units per tube)			
S	MCT5201SM	Surface Mount Lead Bend			
SR2	MCT5201SR2M	Surface Mount; Tape and Reel (1,000 units per reel)			
Т	MCT5201TM	0.4" Lead Spacing			
V	MCT5201VM	IEC60747-5-2			
TV	MCT5201TVM	IEC60747-5-2, 0.4" Lead Spacing			
SV	MCT5201SVM	IEC60747-5-2, Surface Mount			
SR2V	MCT5201SR2VM	IEC60747-5-2, Surface Mount, Tape and Reel (1,000 units per reel)			

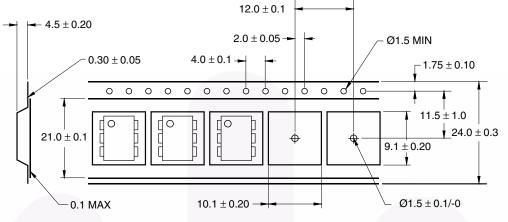
Marking Information



Definitions					
1	Fairchild logo				
2	Device number				
3	VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table)				
4	One digit year code, e.g., '7'				
5	Two digit work week ranging from '01' to '53'				
6	Assembly package code				

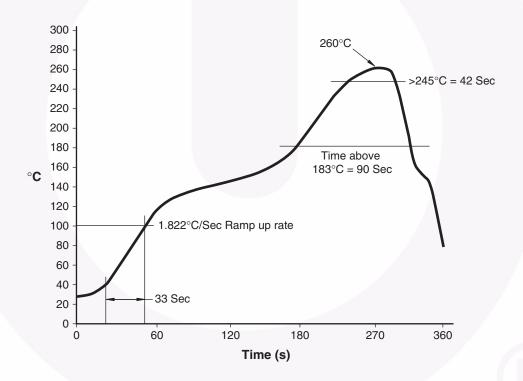
*Note – Parts that do not have the 'V' option (see definition 3 above) that are marked with date code '325' or earlier are marked in portrait format.

Carrier Tape Specification



User Direction of Feed _____

Reflow Profile







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PRODUCT STATUS DEFINITIONS

Definition of Terms

belintation of Terms						
Datasheet Identification	Product Status	Definition				
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.				
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.				
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.				
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.				

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